

# LOGIC DESIGN WITH MOSFETS

Dr. Mohammed Morsy



**Faculty of Engineering  
Alexandria University**



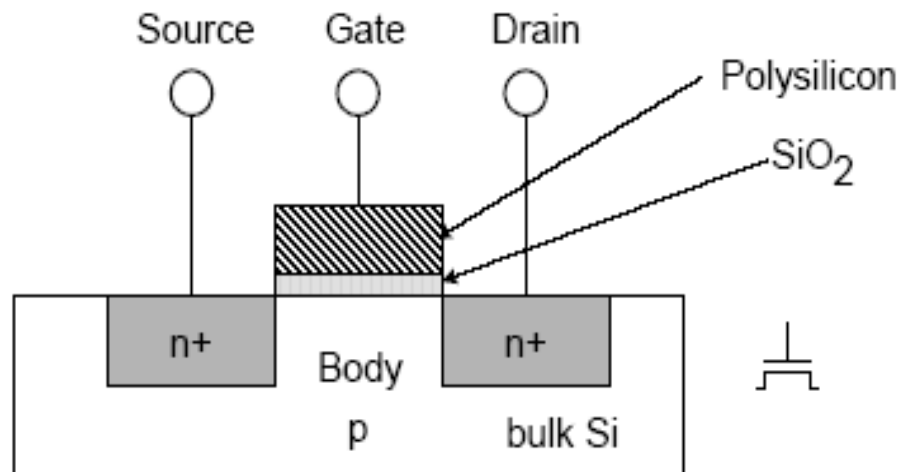
# Outline

- The Fundamental MOSFETs
- Ideal Switches and Boolean Operations
- MOSFETs as Switches
- Basic Logic Gates in CMOS
- Complex Logic Gates in CMOS
- Transmission Gate Circuits



# nMOS Transistor

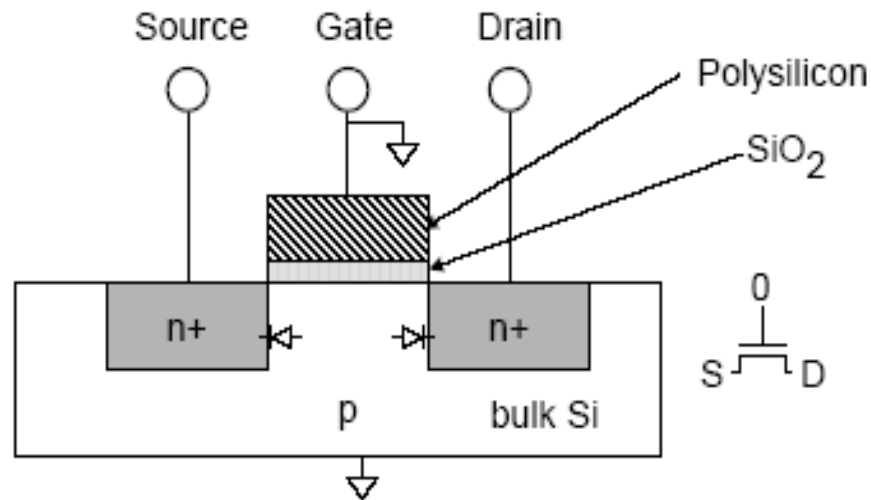
- Four terminals: gate (G), source (S), drain (D), body (B)
- Gate–oxide–body stack looks like a capacitor
  - Gate and body are conductors
  - $\text{SiO}_2$  (oxide) is a very good insulator
  - Called metal – oxide – semiconductor (MOS) capacitor
  - Even though gate is no longer made of metal





# nMOS Operation (1/2)

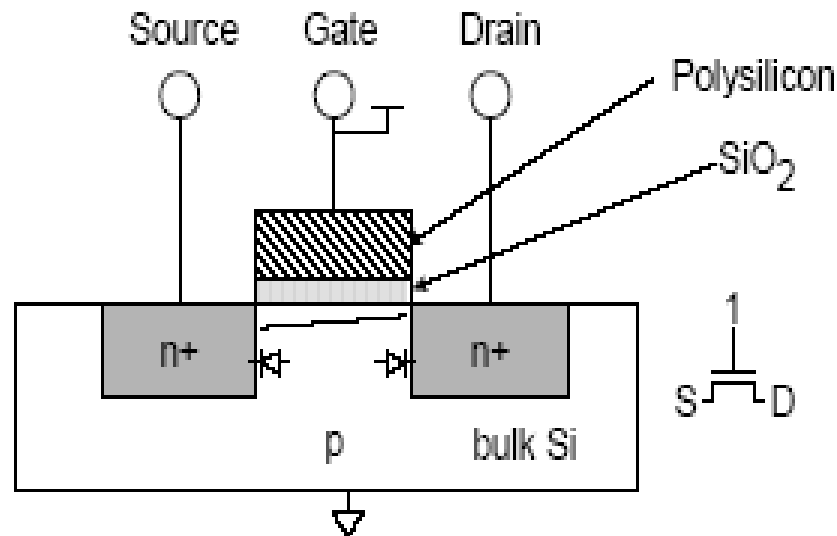
- Body is usually tied to ground (0V)
- When the gate is at a low voltage
  - P-type body is at low voltage
  - Source-body and drain-body diodes are OFF
  - No current flows, transistor is OFF





# nMOS Operation (2/2)

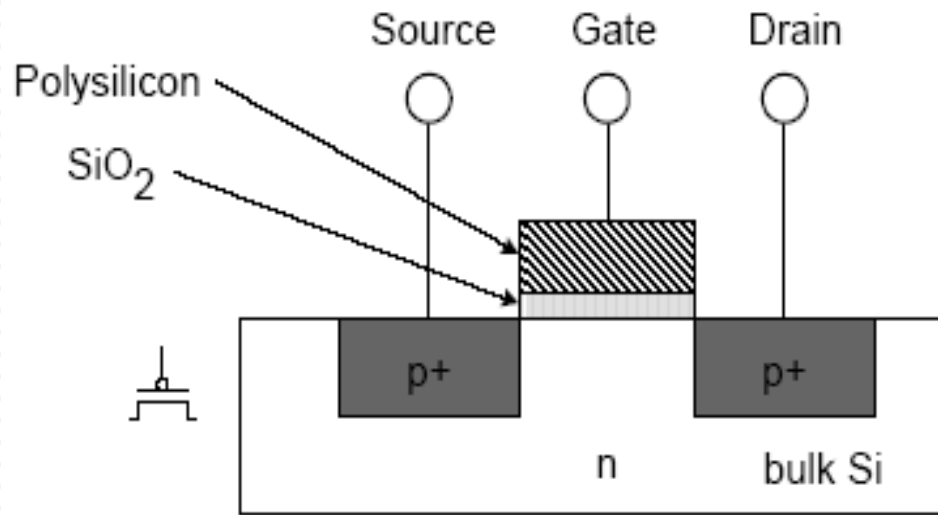
- When the gate is at a high voltage
  - ▣ Positive charge on gate of MOS capacitor
  - ▣ Negative charge attracted to body
  - ▣ Inverts a channel under gate to n-type
  - ▣ Now current can flow through n-type silicon from source through channel to drain, transistor is ON





# pMOS Transistor

- Similar, but doping and voltages reversed
  - Body tied to high voltage (VDD)
  - Gate “low”: transistor ON
  - Gate “high”: transistor OFF
  - Bubble indicates inverted behavior





# Outline

- The Fundamental MOSFETs
- **Ideal Switches and Boolean Operations**
- MOSFETs as Switches
- Basic Logic Gates in CMOS
- Complex Logic Gates in CMOS
- Transmission Gate Circuits



# Ideal Switches (1/3)

- ❑ CMOS integrated circuits use bi-directional devices called MOSFETs as logic switches
  - » Controlled switches, e.g, assert-high and assert-low switches
- ❑ An assert-high switch is showing in Figure 2.1

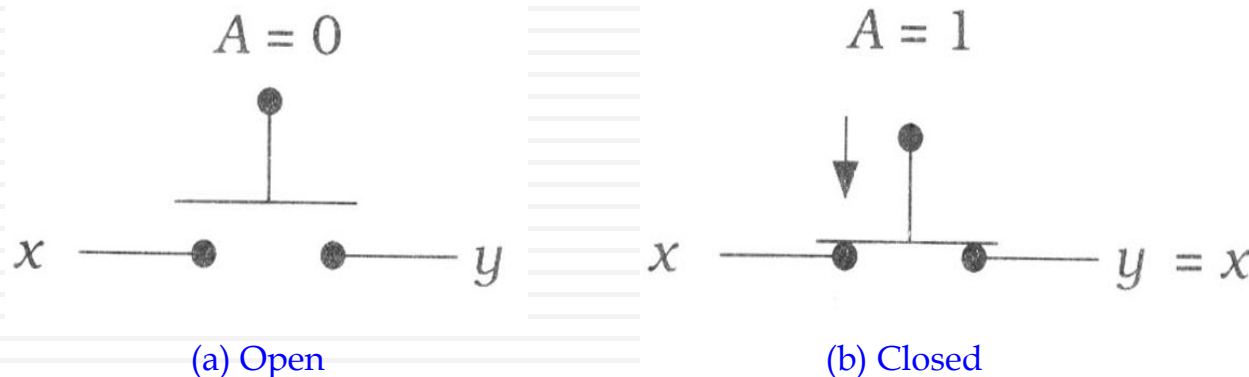
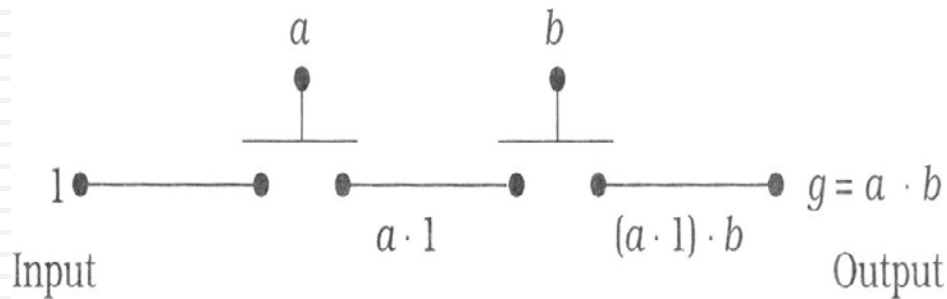


Figure 2.1 Behavior of an assert-high switch



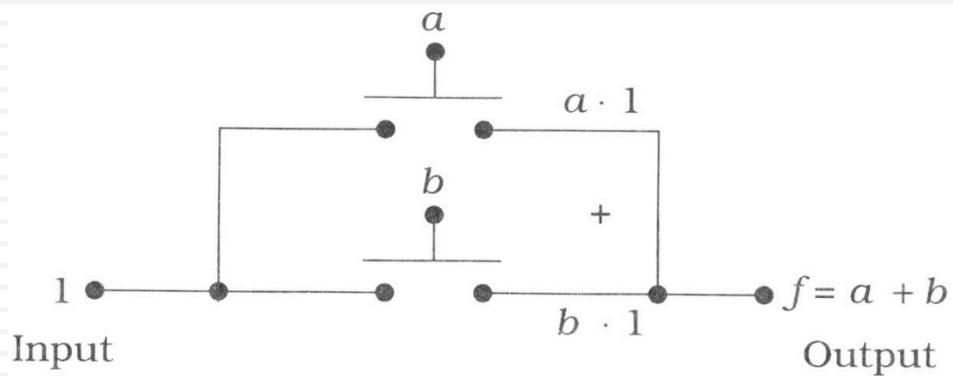


# Ideal Switches (2/3)



$$g = (a \cdot 1) \cdot b = (a \cdot 1) \cdot b$$

Figure 2.2 Series-connected switches

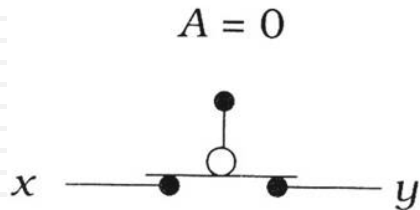


$$g = (a \cdot 1) + (b \cdot 1) = a + b$$

Figure 2.4 Parallel-connected switches



# Ideal Switches (3/3)



(a) Closed

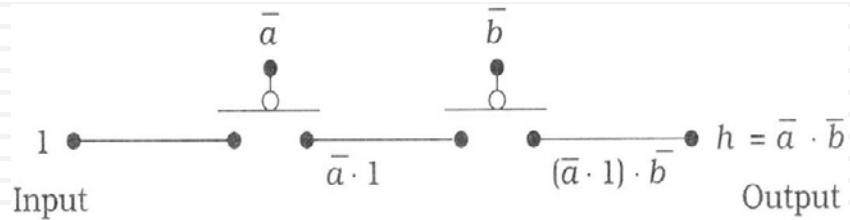
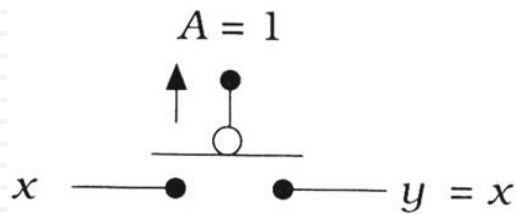


Figure 2.6 Series-connected complementary switches



(b) Open

Figure 2.5 An assert-low switch

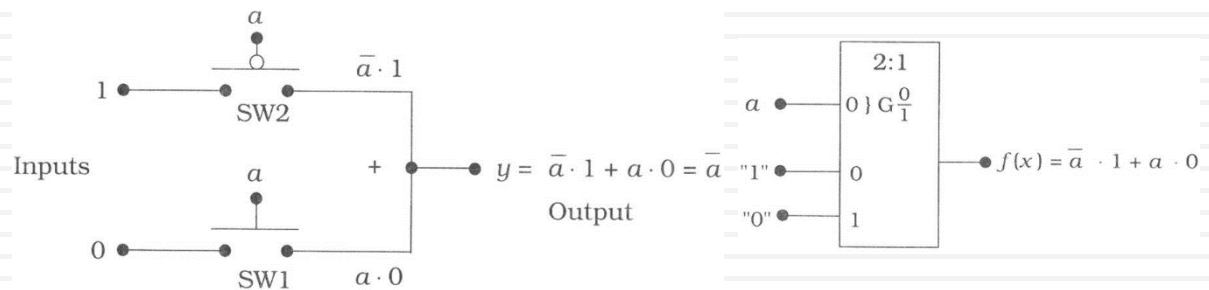


Figure 2.7 An assert-low switch

Figure 2.8 A MUX-based NOT gate



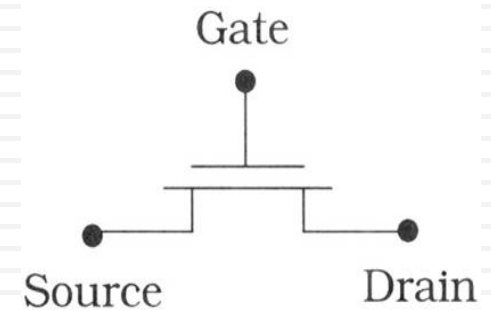
# Outline

- The Fundamental MOSFETs
- Ideal Switches and Boolean Operations
- **MOSFETs as Switches**
- Basic Logic Gates in CMOS
- Complex Logic Gates in CMOS
- Transmission Gate Circuits

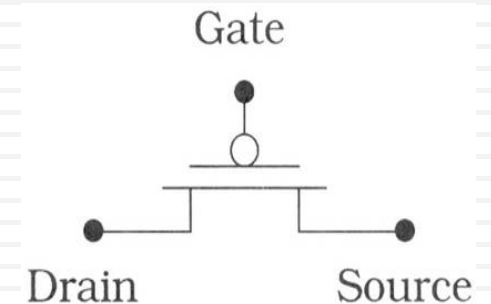


# MOSFET as Switches

- ❑ MOSFET: **M**etal-**O**xide-**S**emiconductor **F**ield-**E**ffect **T**ransistor
- ❑ nFET: an n-channel MOSFET that uses negatively charged electrons for electrical current flow
- ❑ pFET: a p-channel MOSFET that uses positive charges for current flow
- ❑ In many ways, MOSFETs behave like the *idealized switches* introduced in the previous section
- ❑ The voltage applied to the gate determines the current flow between the source and drain terminals



(a) nFET symbol



(b) pFET symbol

Figure 2.9 Symbols used for nFETs and pFETs

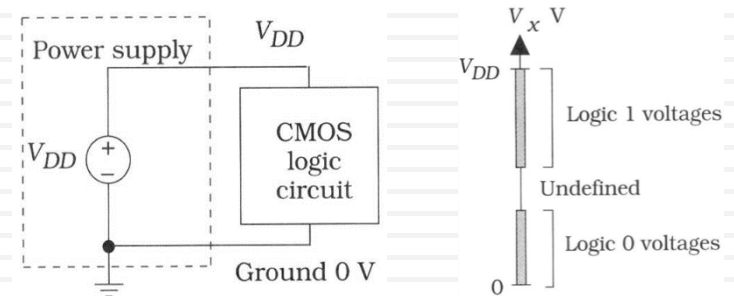
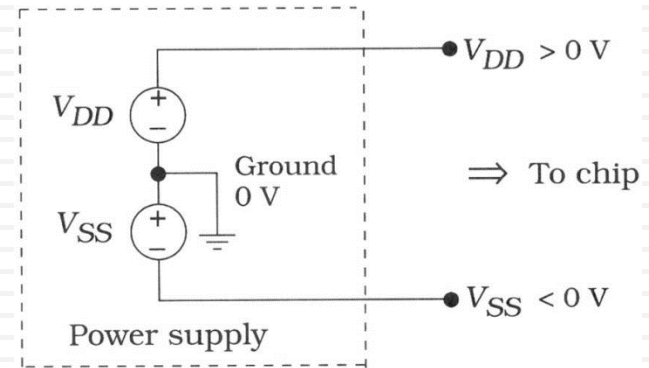


# MOSFET as Switches

- Early generations of silicon MOS logic circuits used both *positive* and *negative supply voltages* as Figure 2.10 showing
- Modern designs require only a single positive voltage  $V_{DD}$  and the ground connection, e.g.  $V_{DD} = 5\text{ V}$  and  $3.3\text{ V}$  or lower
- The relationship between logic variables  $x$  and its voltages  $V_x$

$$0 \leq V_x \leq V_{DD} \quad (2.14)$$

$$\begin{cases} x = 0 \text{ means that } V_x = 0\text{V} \\ x = 1 \text{ means that } V_x = V_{DD} \end{cases} \quad (2.15)$$



(a) Power supply connection (b) Logic definitions

Figure 2.11 Single voltage power supply



# Switching Characteristics of MOSFET

- In general,
  - Low voltages correspond to logic 0 values
  - High voltages correspond to logic 1 values
- The transition region between the highest logic 0 voltage and the lowest logic 1 voltage is undefined

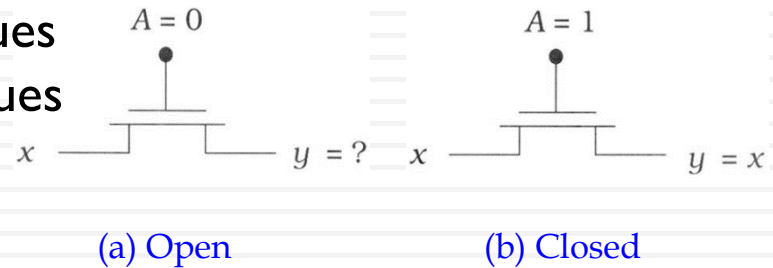


Figure 2.12 nFET switching characteristics

## □ nFET

$$y = x \cdot A \text{ which is valid iff } A = 1 \quad (2.16)$$

## □ pFET

$$y = x \cdot \bar{A} \text{ which is valid iff } A = 0 \quad (2.17)$$

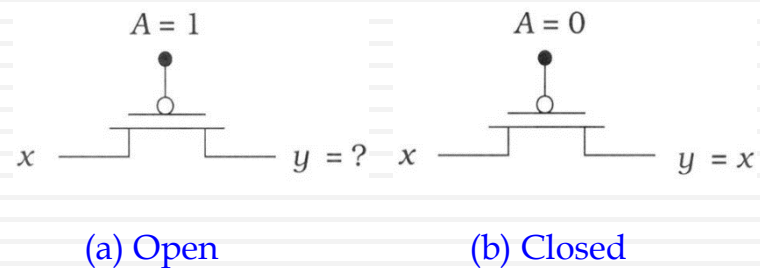


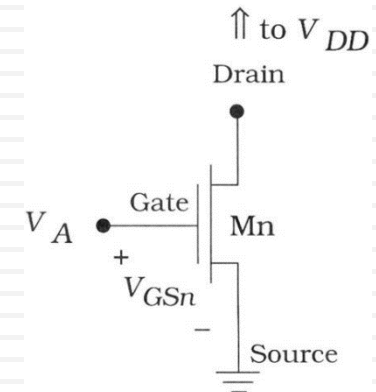
Figure 2.13 pFET switching characteristics



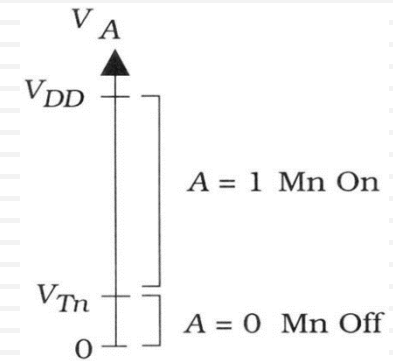
# nMOS FET Threshold Voltages

- An nFET is characterized by a threshold voltage  $V_{Tn}$  that is positive, typical is around  $V_{Tn} = 0.5\text{ V}$  to  $0.7\text{ V}$
- If  $V_{GSn} \leq V_{Tn}$ , then the transistor acts like an open (**off**) circuit and there is no current flow between the drain and source
- If  $V_{GSn} \geq V_{Tn}$ , then the nFET drain and source are connected and the equivalent switch is closed (**on**)
- Thus, to define the voltage  $V_A$  that is associated with the binary variable  $A$

$$V_A = V_{GSn} \quad (2.20)$$



(a) Gate-source voltage



(b) Logic translation

Figure 2.14 Threshold voltage of an nFET



# pMOS FET Threshold Voltages

- An pFET is characterized by a threshold voltage  $V_{Tp}$  that is negative, typical is around  $V_{Tp} = -0.5\text{ V}$  to  $-0.8\text{ V}$ 
  - If  $V_{SGp} \leq |V_{Tp}|$ , then the transistor acts like an open (**off**) switch and there is no current flow between the drain and source
  - If  $V_{SGp} \geq |V_{Tp}|$ , then the pFET drain and source are connected and the equivalent switch is closed (**on**)
- Thus, to the applied voltage  $V_A$  we first sum voltage to write

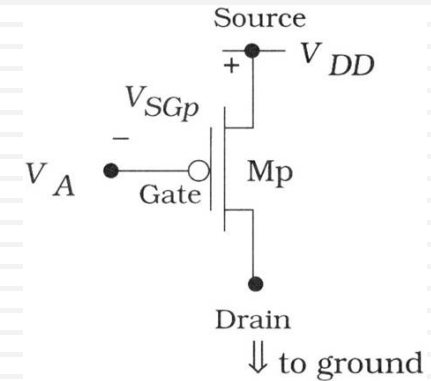
$$V_A + V_{SGp} = V_{DD} \quad (2.23)$$

$$\Rightarrow V_A = V_{DD} - V_{SGp} \quad (2.24)$$

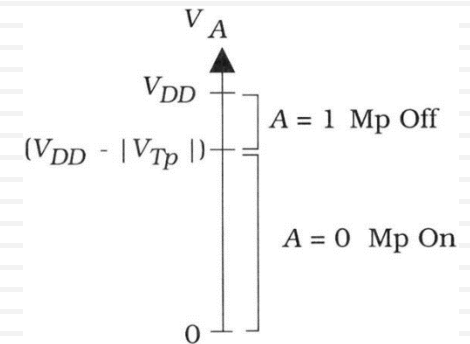
$$\left\{ \begin{array}{l} V_A = 0\text{ V} \\ V_A = V_{DD} \end{array} \right. \quad (2.26)$$

$$V_{DD} - |V_{Tp}| \quad (2.25)$$

Note that the transition between a logic 0 and a logic 1 is at Eqn (2.25) !



(a) Source-gate voltage



(b) Logic translation

Figure 2.15 pFET threshold voltage





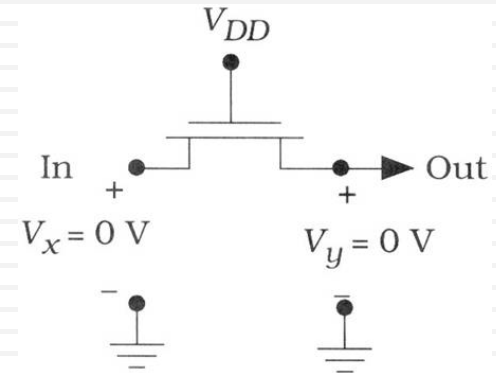
# nFET Pass Characteristics

- An ideal electrical switch can pass any voltage applied to it
- As Figure 2.16(b), the output voltage  $V_y$  is reduced to a value

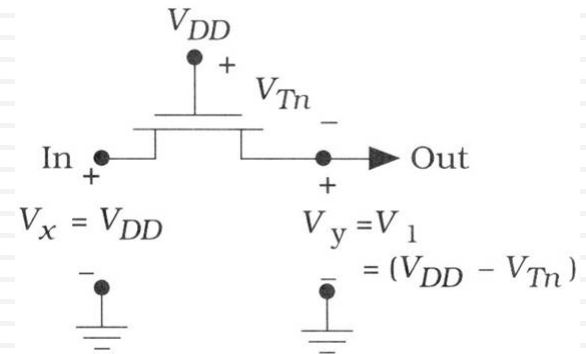
$$V_1 = V_{DD} - V_{Tn} \quad (2.27) \quad \text{since} \quad V_{GSn} = V_{Tn}$$

which is less than the input voltage  $V_{DD}$ , called **threshold voltage loss**

- Thus, we say that the nFET can only pass a **weak logic 1**; in other word, the nFET is said to pass a **strong logic 0** → can pass a voltage in the range  $[0, V_1]$



(a) Logic 0 transfer



(b) Logic 1 transfer

Figure 2.16 nFET pass characteristics



# pFET Pass Characteristics

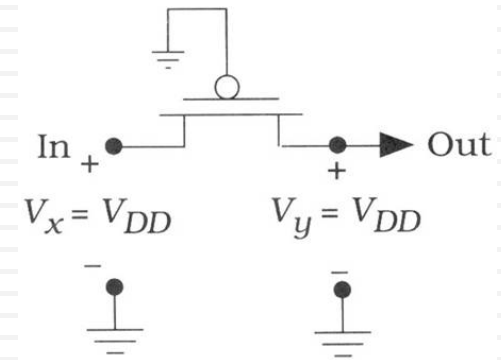
- Figure 2.17(a) portrays the case where  $V_x = V_{DD}$  corresponding to a logic 1 input. The output voltage is

$$V_y = V_{DD} \quad (2.29) \text{ , which is an ideal logic 1 level}$$

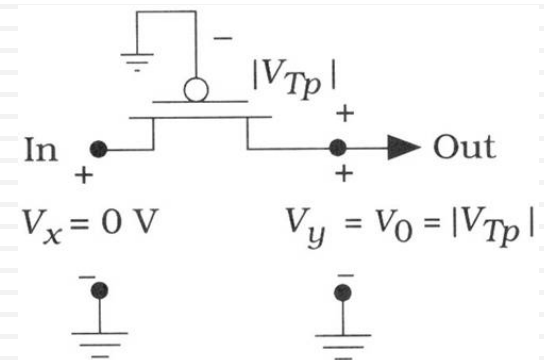
- Figure 2.17(b), the transmitted voltage can only drop to a minimum value of

$$V_y = |V_{Tp}| \quad (2.30) \text{ since } V_{SGp} = |V_{Tp}|$$

- The results of the above discussion
  - nFETs pass strong logic 0 voltages, but weak logic 1 values
  - pFETs pass strong logic 1 voltages, but weak logic 0 levels
  - Use pFETs to pass logic 1 voltages of  $V_{DD}$
  - Use nFETs to pass logic 0 voltages of  $V_{SS} = 0V$



(a) Logic 0 transfer



(b) Logic 1 transfer

Figure 2.17 pFET pass characteristics



# Outline

- The Fundamental MOSFETs
- Ideal Switches and Boolean Operations
- MOSFETs as Switches
- **Basic Logic Gates in CMOS**
- Complex Logic Gates in CMOS
- Transmission Gate Circuits



# Basic Logic Gates in CMOS

- Digital logic circuits are nonlinear networks that use transistors as electronic switches to divert one of the supply voltages  $V_{DD}$  or 0 V to the output
- The general switching network

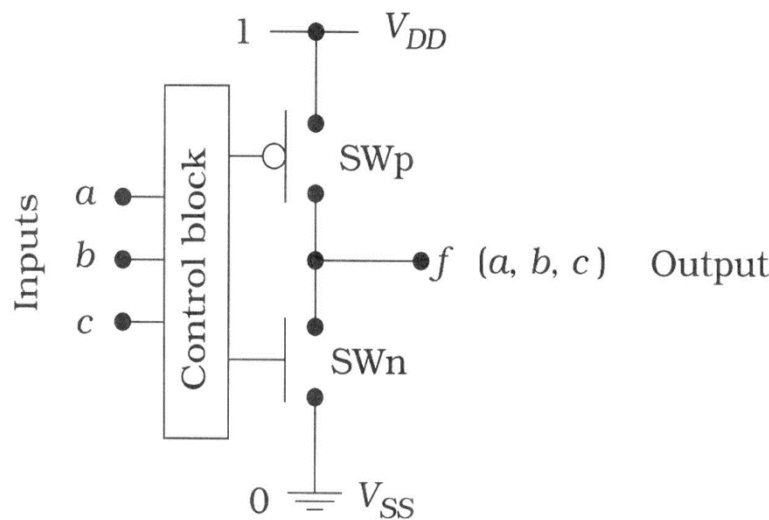
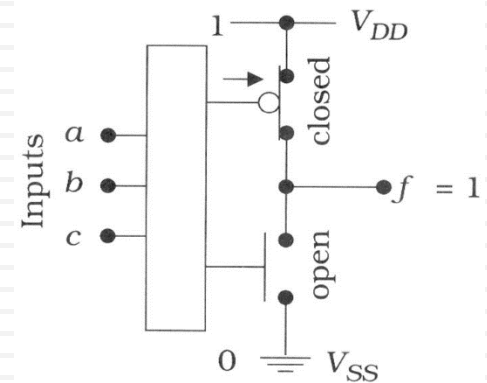
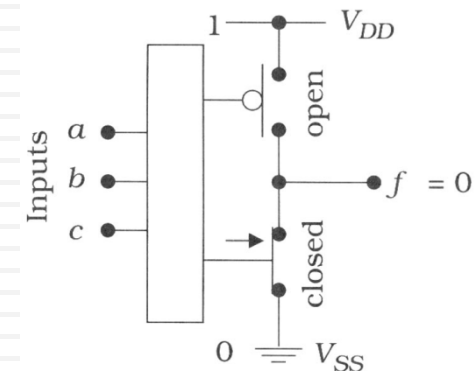


Figure 2.18 General CMOS logic gate



(a)  $f = 1$  output



(b)  $f = 0$  output

Figure 2.19 Operation of a CMOS logic gate



# The NOT Gate (1/2)

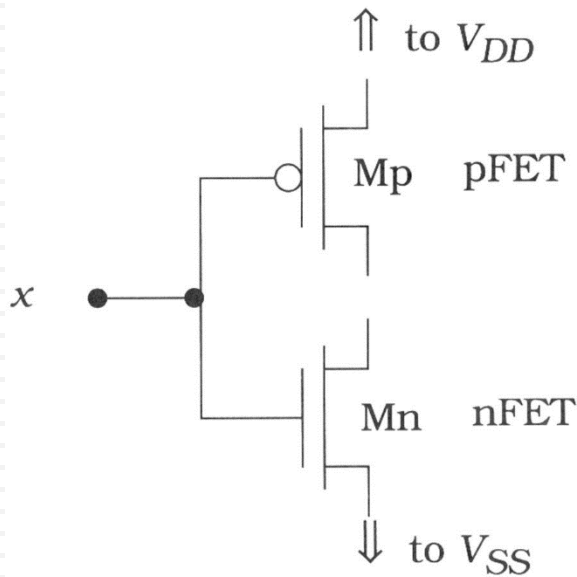
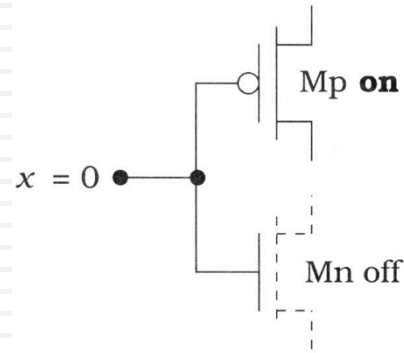
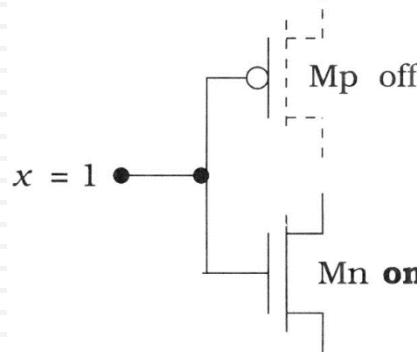


Figure 2.20 A complementary pair

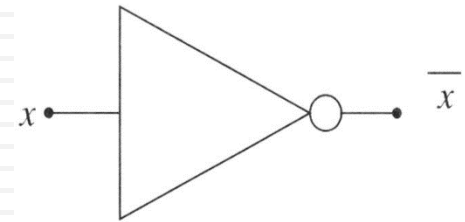


(a)  $x = 0$  input



(b)  $x = 1$  input

Figure 2.21 Operation of the complementary pair



(a) Logic symbol

$x$	$\overline{x}$
0	1
1	0

(b) Truth Table

Figure 2.22 NOT gate



# The NOT Gate (2/2)

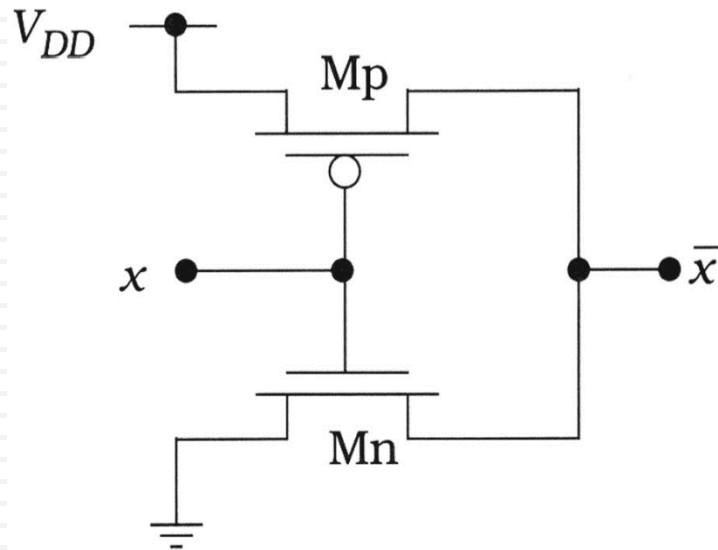
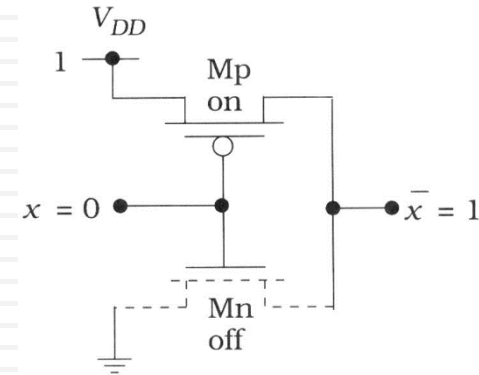
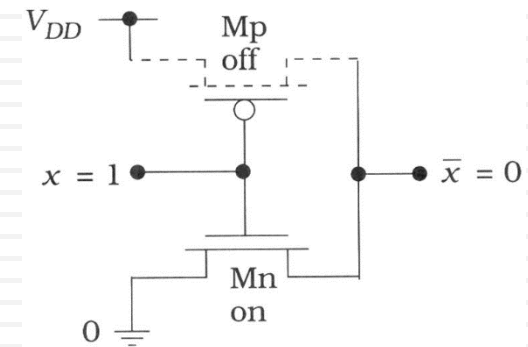


Figure 2.23 CMOS not gate



(a)  $x = 0$  input

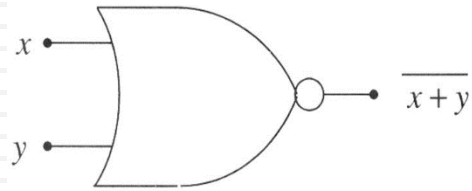


(b)  $x = 1$  input

Figure 2.24 Operation of the CMOS NOT gate



# The NOR Gate (1/2)

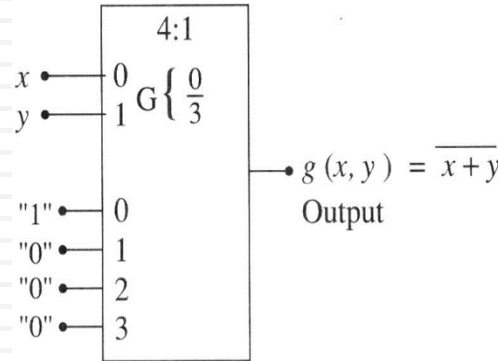


(a) Logic symbol

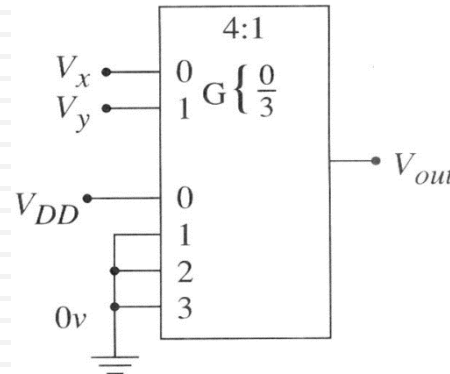
x	y	$\overline{x+y}$
0	0	1
0	1	0
1	0	0
1	1	0

(b) Truth Table

Figure 2.25 NOR logic gate



(a) Logic diagram



(b) Voltage network

Figure 2.26 NOR2 using a 4:1 multiplexor

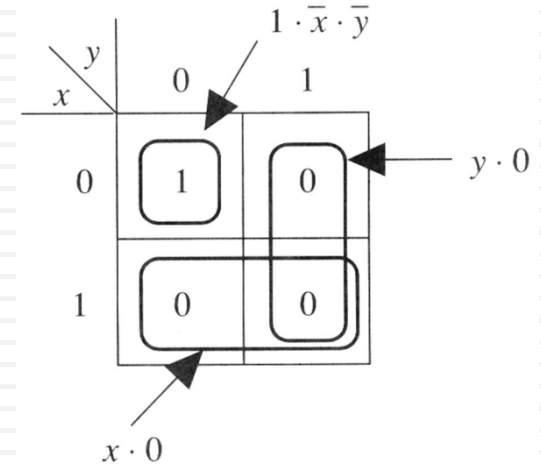


Figure 2.27 NOR2 gate Karnaugh map



# NOR (2/2)

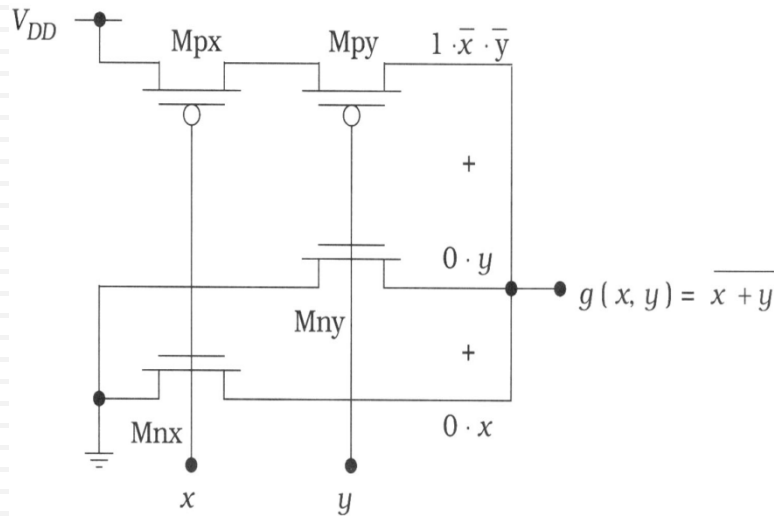


Figure 2.28 NOR2 in CMOS

$x$	$y$	Mpx	Mpy	Mnx	Mny	$g$
0	0	on	on	off	off	1
0	1	on	off	off	on	0
1	0	off	on	on	off	0
1	1	off	off	on	on	0

Figure 2.29 Operational summary of the NOR2 gate

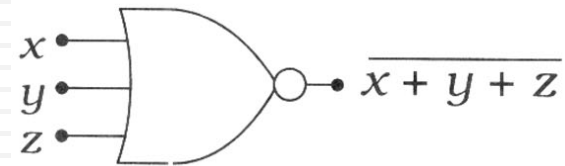
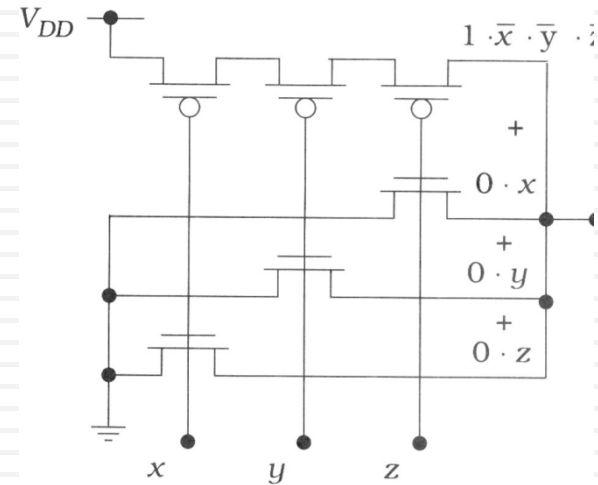
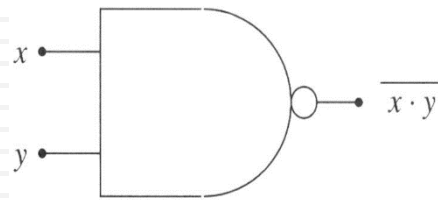


Figure 2.30 NOR3 in CMOS





# NAND (1/2)

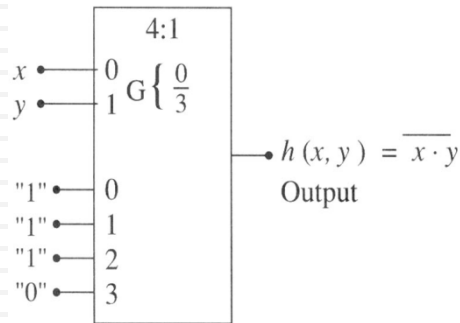


(a) Logic symbol

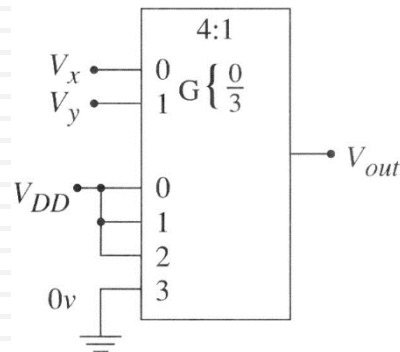
$x$	$y$	$\overline{x \cdot y}$
0	0	1
0	1	1
1	0	1
1	1	0

(b) Truth Table

Figure 2.31 NAND2 logic gate



(a) Logic diagram



(b) Voltage network

Figure 2.32 NAND2 using 4:1 multiplexor

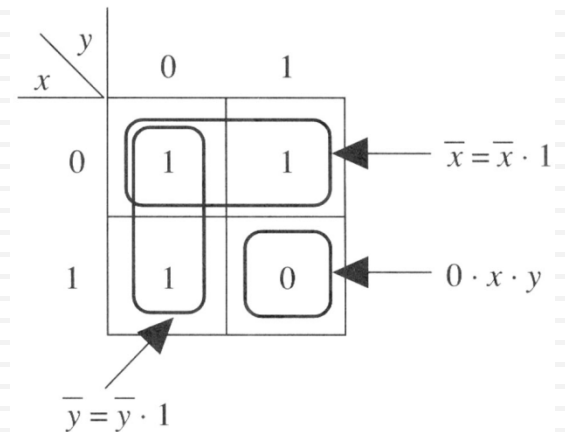


Figure 2.33 NAND2 K-map



# NAND (2/2)

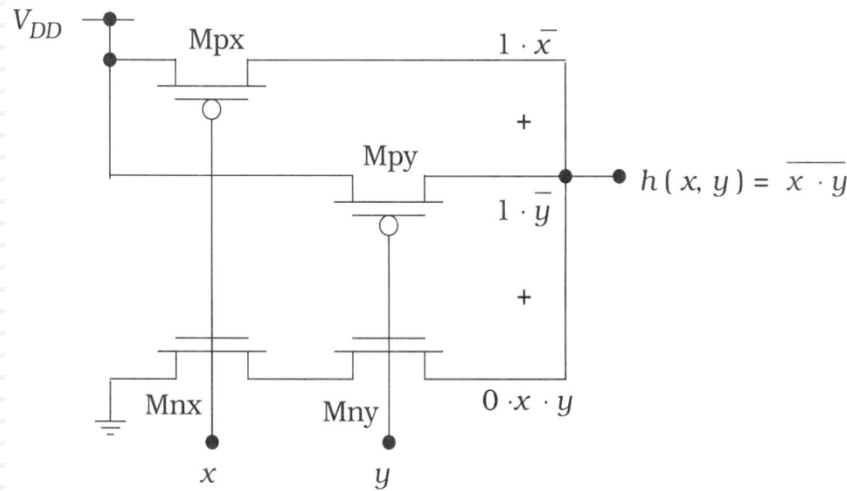


Figure 2.34 CMOS NAND2 logic circuit

$x$	$y$	Mpx	Mpy	Mnx	Mny	$h$
0	0	on	on	off	off	1
0	1	on	off	off	on	1
1	0	off	on	on	off	1
1	1	off	off	on	on	0

Figure 2.35 Operational summary of the NAND2 gate

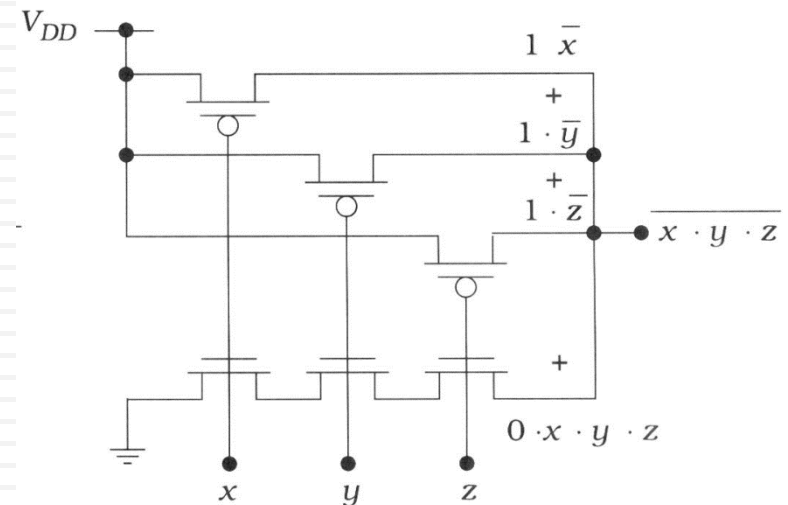
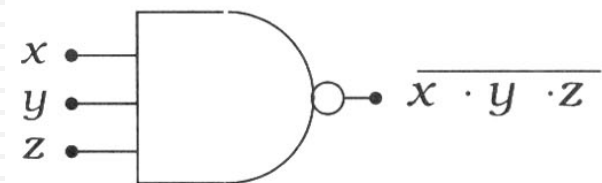


Figure 2.36 NAND3 in CMOS





# Outline

- The Fundamental MOSFETs
- Ideal Switches and Boolean Operations
- MOSFETs as Switches
- Basic Logic Gates in CMOS
- **Complex Logic Gates in CMOS**
- Transmission Gate Circuits

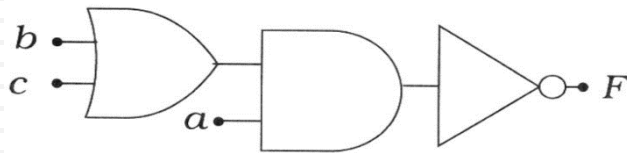


# Complex Logic Gate (1/3)

- Complex or combinational logic gates

- Useful in VLSI system-level design

- Consider a Boolean expression  $F(a,b,c) = \overline{a \cdot (b + c)}$



$$\begin{aligned} F(a,b,c) &= \overline{a \cdot (b + c)} \\ &= \overline{a} + \overline{(b + c)} && (2.50) \\ &= [\overline{a} + (\overline{b} \cdot \overline{c})] \cdot 1 \end{aligned}$$

- Expanding by simply ANDing the result with a logical 1

$$F = \overline{a} \cdot 1 + (\overline{b} \cdot \overline{c}) \cdot 1 \quad (2.51)$$



# Complex Logic Gate (2/3)

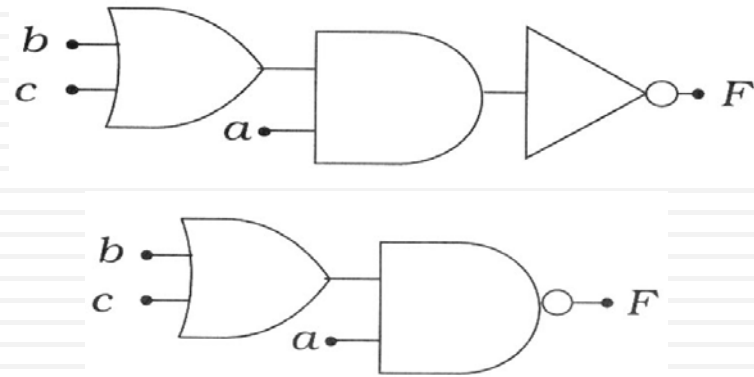


Figure 2.37 Logic function example

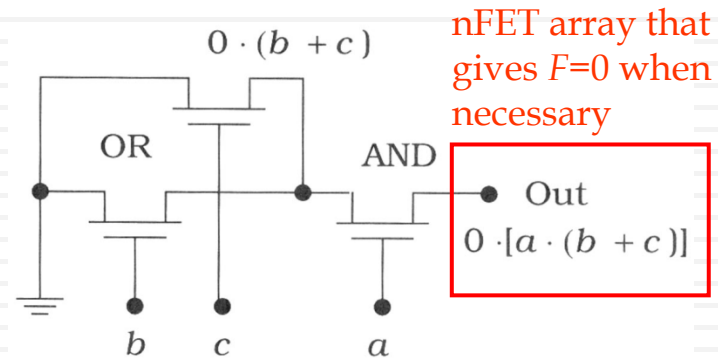


Figure 2.39 nFET circuit for F

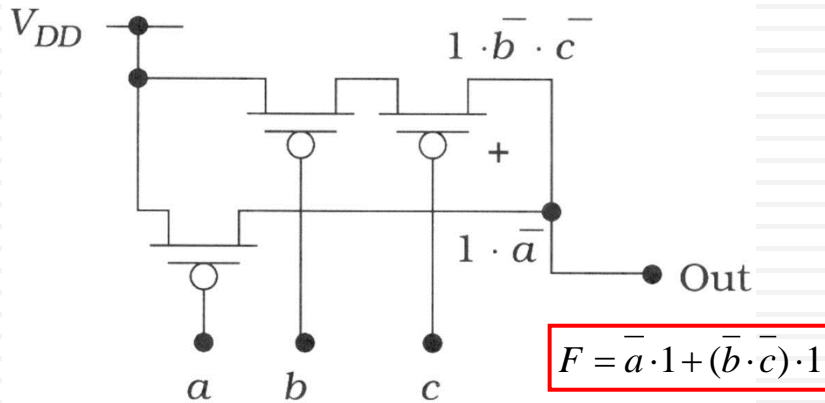


Figure 2.38 pFET circuit for F function from equation (2.51)

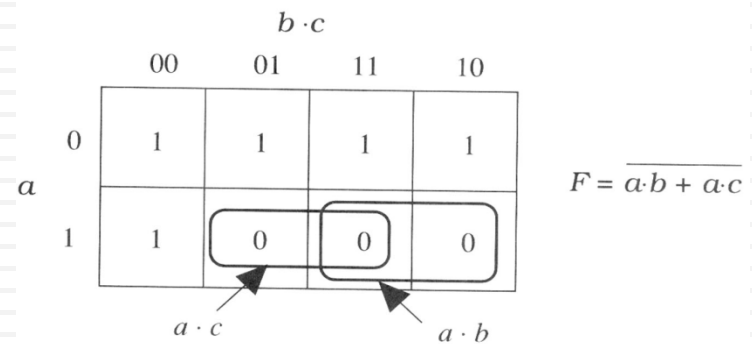


Figure 2.40 Karnaugh for nFET circuit



# Complex Logic Gate (3/3)

- ❑ The characteristics of Complementary CMOS
  - ❑ For CMOS circuits, due to the completely symmetrical structure, if the input voltage is  $0 \sim V_{DD}$  (full swing), the output signal is also  $V_{DD}$  to  $0$  (inverting) the full-swing (strong output levels).
  - ❑ There is no static power consumption.
  - ❑ Process variations will not affect the full swing output of CMOS circuits. Such variations would perhaps affect the electrical characteristics such as the speed or power consumption, etc., but do not affect its proper function. This feature leverages reliable mass production of CMOS VLSI circuits.

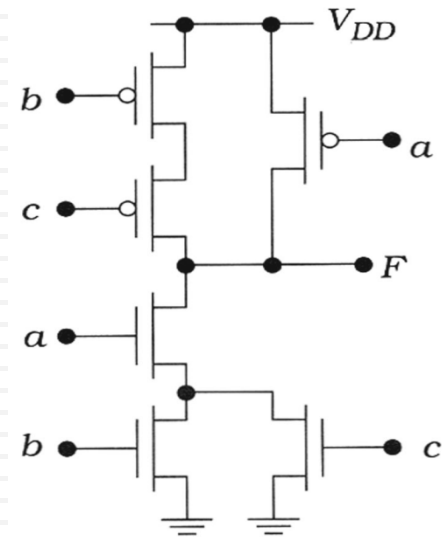


Figure 2.41 Finished complex CMOS logic circuit



# Structured Logic Design (1/4)

- CMOS logic gates are intrinsically **inverting**
  - Output always produces a *NOT* operation acting on the input variables

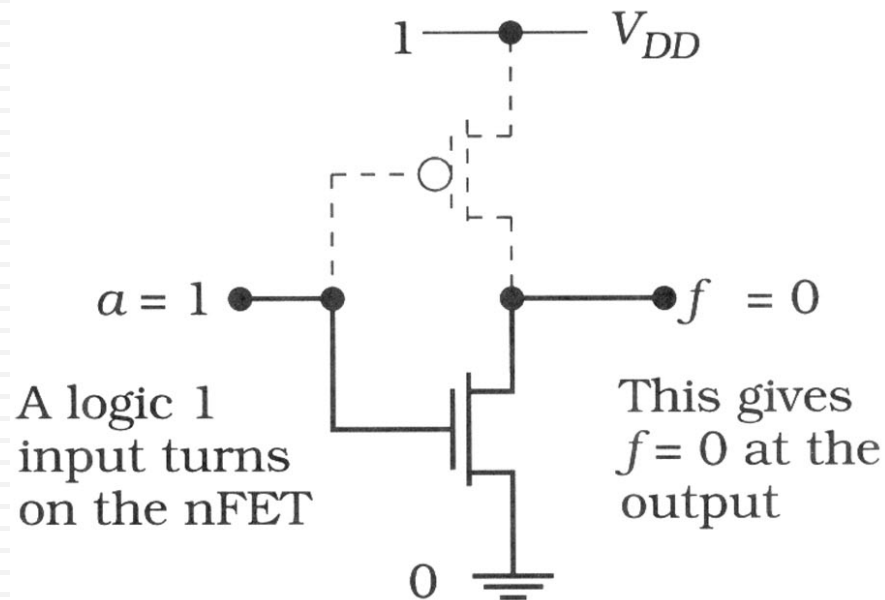
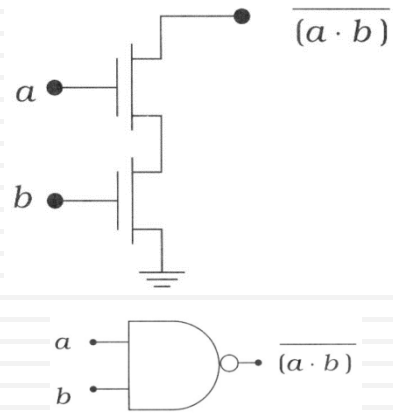


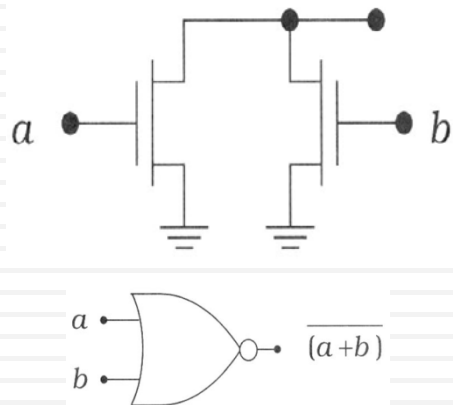
Figure 2.42 Origin of the inverting characteristic of CMOS gates



# Structured Logic Design (2/4)



(a) Series-connected nFETs



(b) Parallel-connected nFETs

Figure 2.43 nFET logic formation

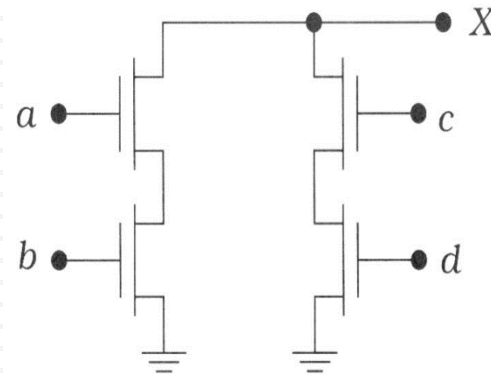


Figure 2.44 nFET AOI circuit

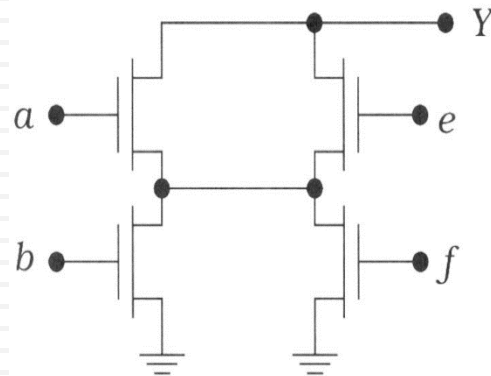
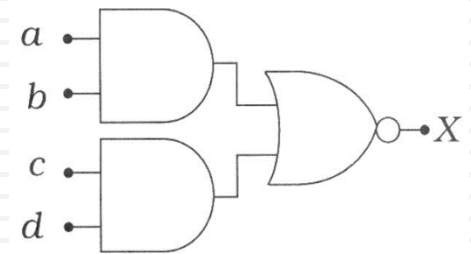
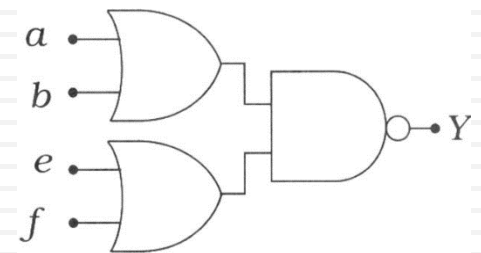


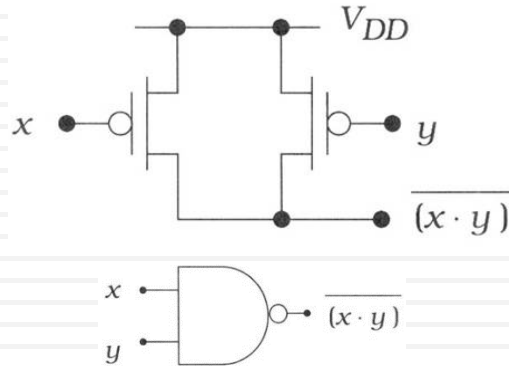
Figure 2.45 nFET OAI circuit



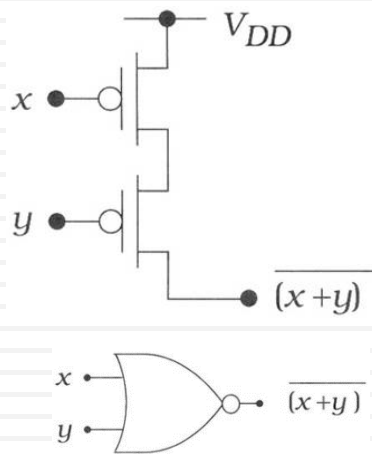




# Structured Logic Design (3/4)

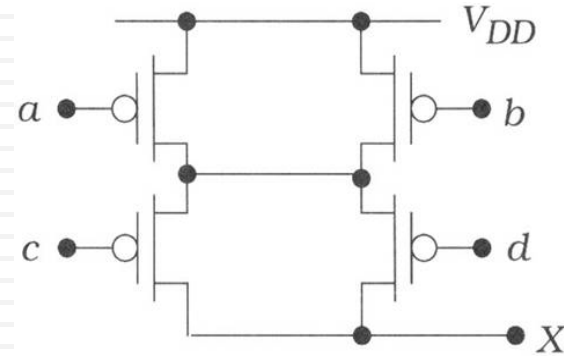


(a) Parallel-connected pFETs

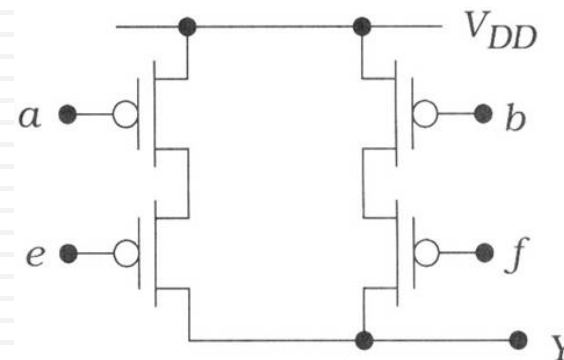


(b) Series-connected pFETs

Figure 2.46 pFET logic formation



(a) pFET AOI circuit

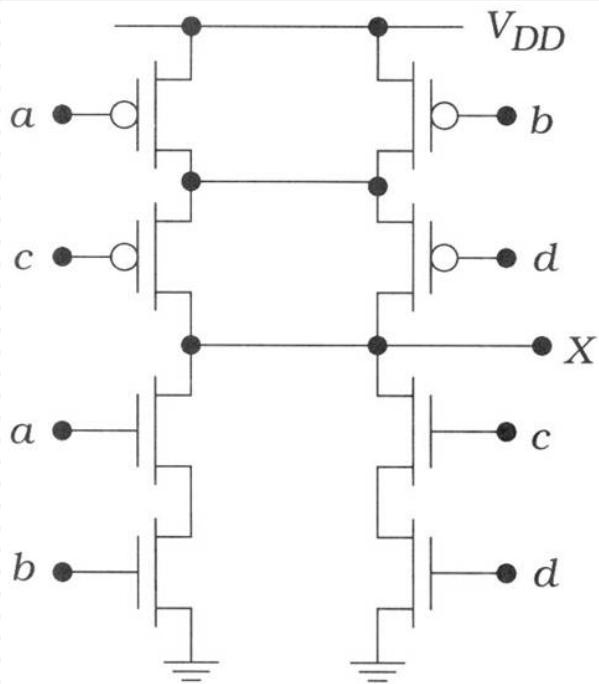


(b) pFET OAI circuit

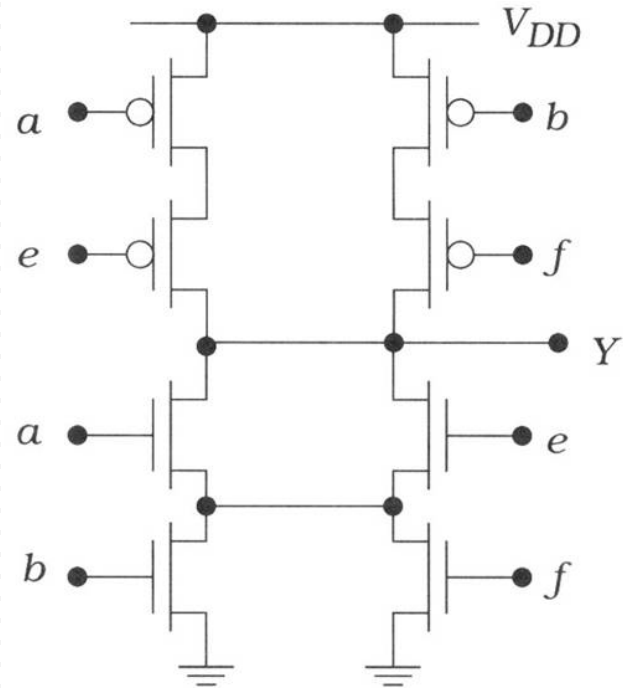
Figure 2.47 pFET arrays for AOI and OAI gates



# Structured Logic Design (4/4)



(a) AOI circuit

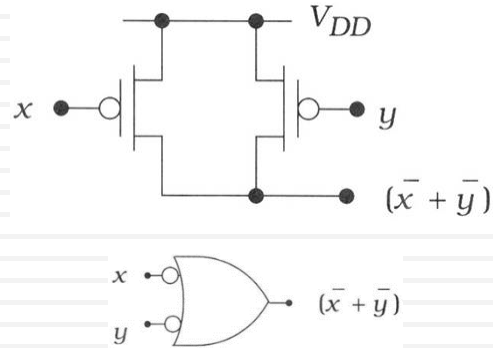


(b) OAI circuit

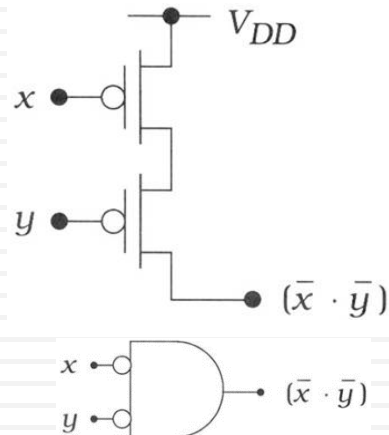
Figure 2.48 Complete CMOS AOI and OAI circuits



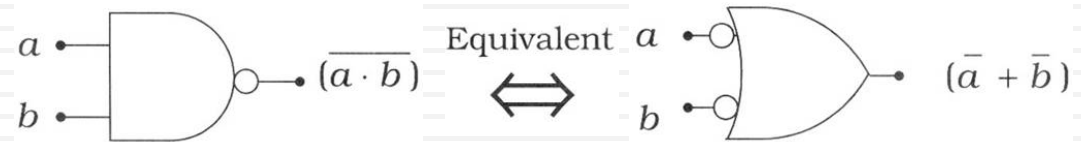
# Bubble Pushing



(a) Parallel-connected pFETs



(b) Series-connected pFETs



(a) NAND - OR



(b) NOR - AND

Figure 2.52 Bubble pushing using DeMorgan rules

Figure 2.51 Assert-low models for pFETs



# XOR and XNOR Gates

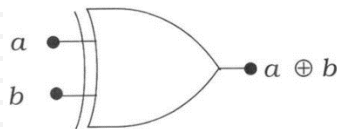
- An important example of using an AOI circuit is constructing Exclusive-OR (XOR) and Exclusive-NOR circuits

$$a \oplus b = \bar{a} \cdot b + a \cdot \bar{b} \quad (2.71)$$

$$\overline{a \oplus b} = a \cdot b + \bar{a} \cdot \bar{b} \quad (2.72)$$

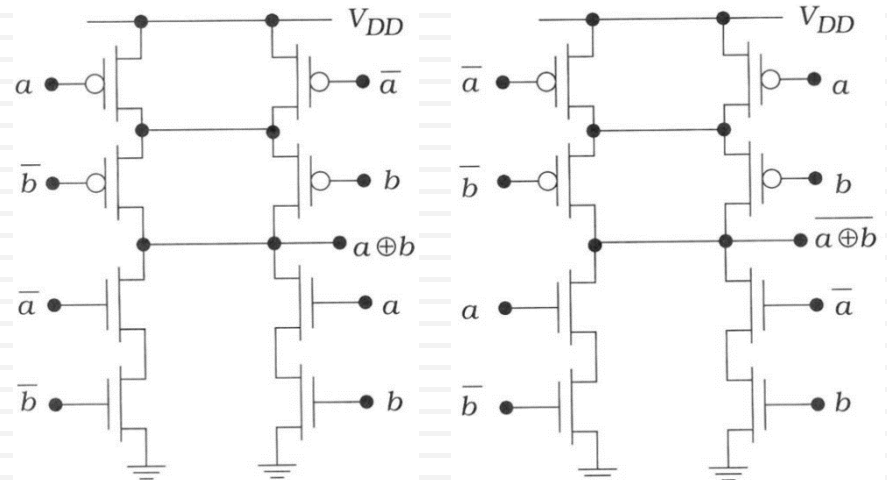
$$\Rightarrow a \oplus b = \overline{\overline{a \oplus b}} = \overline{a \cdot b + \bar{a} \cdot \bar{b}} \quad (2.73)$$

$$\Rightarrow \overline{a \oplus b} = \bar{a} \cdot b + a \cdot \bar{b} \quad (2.74)$$



a	b	$a \oplus b$
0	0	0
0	1	1
1	0	1
1	1	0

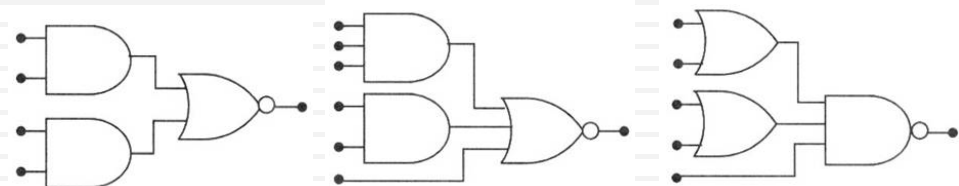
Figure 2.56 XOR



(a) Exclusive-OR

(b) Exclusive-NOR

Figure 2.57 AOI XOR and XNOR gates



(a) AOI22

(b) AOI321

(c) AOI221

Figure 2.58 General naming convention



# Outline

- The Fundamental MOSFETs
- Ideal Switches and Boolean Operations
- MOSFETs as Switches
- Basic Logic Gates in CMOS
- Complex Logic Gates in CMOS
- **Transmission Gate Circuits**



# Transmission Gate Circuits

- A CMOS TG is created by connecting an nFET and pFET in parallel
  - Bi-directional
  - Transmit the entire voltage range  $[0, V_{DD}]$

$$y = x \cdot s \quad \text{iff} \quad s = 1 \quad (2.78)$$

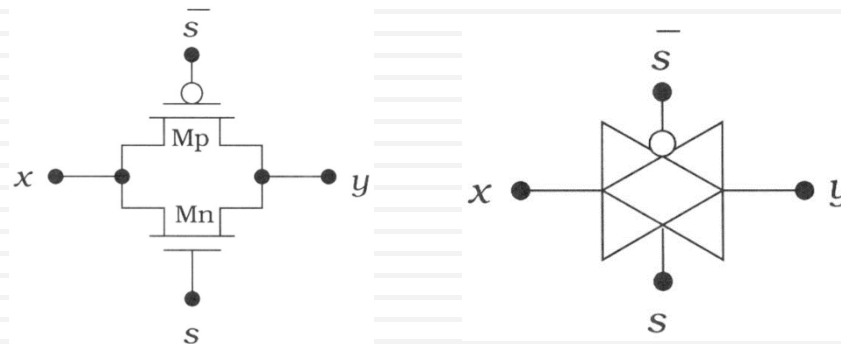


Figure 2.60 Transmission gate (TG)



# Logic Design using TG (1/3)

## □ Multiplexors

### ▣ TG based 2-to-1 multiplexor

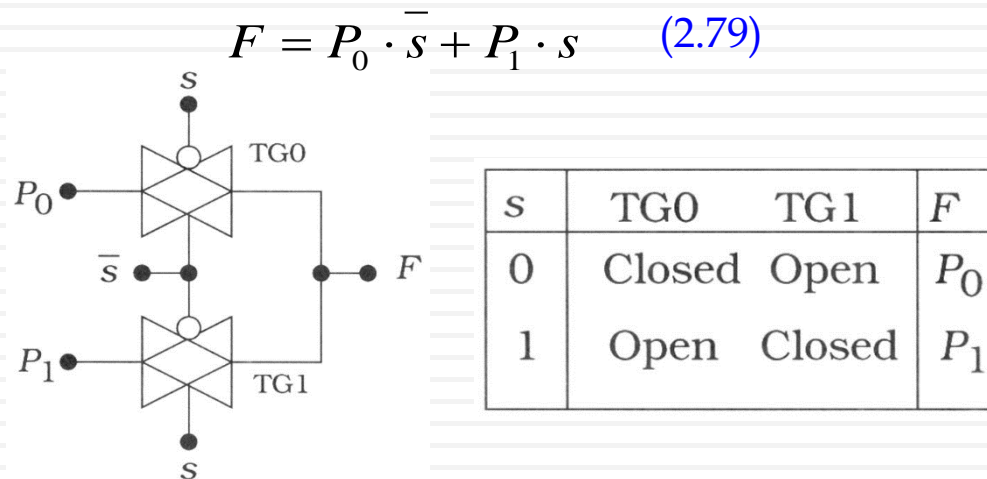


Figure 2.61 A TG-based 2-to-1 multiplexor

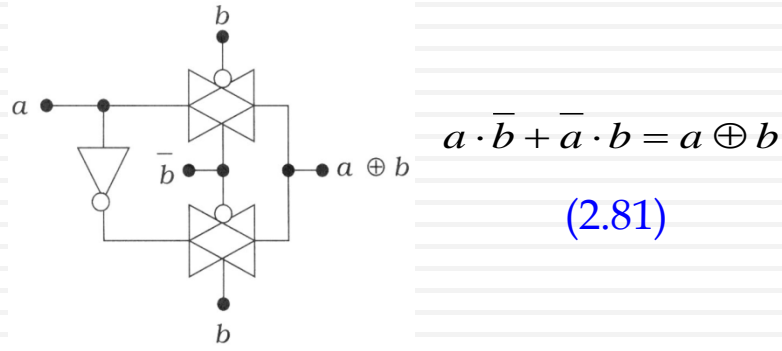
### ▣ The 2-to-1 extended to a 4:1 network by using the 2-bit selector word ( $s_1, s_0$ )

$$F = P_0 \cdot \bar{s}_1 \cdot \bar{s}_0 + P_1 \cdot \bar{s}_1 \cdot s_0 + P_2 \cdot s_1 \cdot \bar{s}_0 + P_3 \cdot s_1 \cdot s_0 \quad (2.80)$$



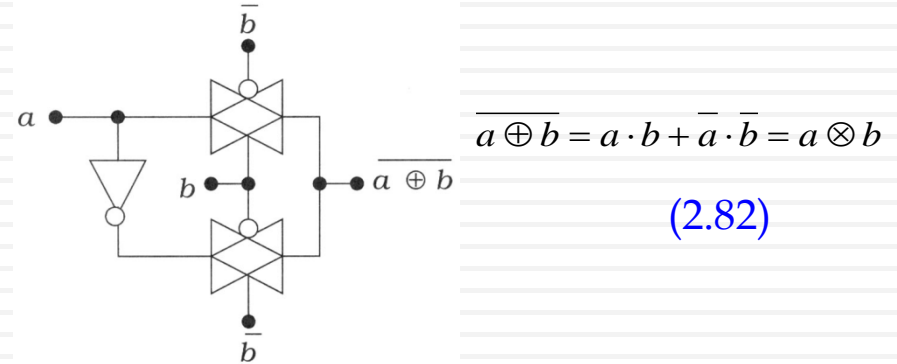
# Logic Design using TG (2/3)

## □ TG based XOR/XNOR



(a) XOR circuit

$$a \cdot \bar{b} + \bar{a} \cdot b = a \oplus b \quad (2.81)$$



(b) XNOR circuit

$$\overline{a \oplus b} = a \cdot b + \bar{a} \cdot \bar{b} = a \otimes b \quad (2.82)$$

Figure 2.62 TG-based exclusive-OR and exclusive-NOR circuits

## □ TG based OR gate

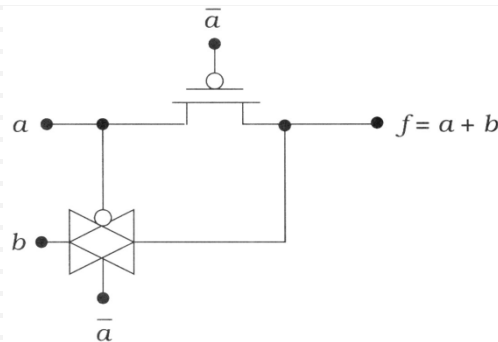


Figure 2.63 A TG-based OR gate

$$\begin{aligned} f &= a \cdot (\bar{a}) + \bar{a} \cdot b \\ &= a + \bar{a} \cdot b \\ &= a + b \end{aligned} \quad (2.83)$$





# Logic Design using TG (3/3)

- Alternate XOR/XNOR Circuits
  - Mixing TGs and FETs which are designed for exclusive-OR and equivalence (XNOR) functions
  - It's important in adders and error detection/correction algorithms

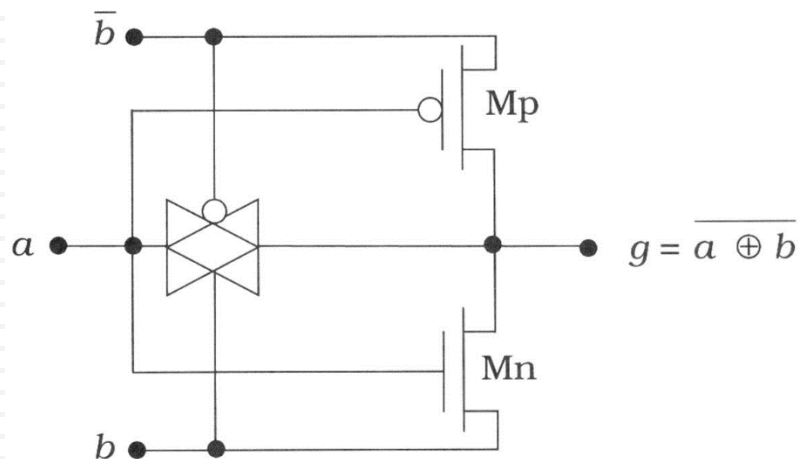


Figure 2.64 An XNOR gate that used both TGs and FETs